IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-59(Canceled)

60. (Currently Amended) A method for manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming an insulating film comprising a resin over the plurality of thin film transistors;

forming a passivation film over the insulating film; and

forming an electroluminescence element over the passivation film, said electroluminescence element comprising a first electrode formed [[on]] in contact with the passivation film, a light emitting layer formed on the first electrode by an ink jet method and a second electrode formed on the light emitting layer,

wherein said first electrode is electrically connected to one of said thin film transistors through a contact hole through said passivation film and said insulating film.

61. (Canceled)

62. (Currently Amended) A method according to claim 60 wherein the passivation film comprises an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), or an insulating film that comprises Si, Al, N, O

and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), ~~(La) lanthanum~~ La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

63. (Previously presented) A method according to claim 60 wherein said passivation film comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

64. (Previously presented) A method according to claim 60 wherein said electroluminescence material comprises an organic light emitting layer.

65. (Currently Amended) A method for manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming an insulating film comprising a resin over the plurality of thin film transistors;

forming a first passivation film over the insulating film;

forming an electroluminescence element over the first passivation film, said electroluminescence element comprising ~~an anode, a cathode~~ a first electrode formed in contact with the first passivation film, a second electrode and a light emitting layer interposed therebetween; and

forming a second passivation film over the electroluminescence element,

wherein the light emitting layer, the second electrode and the second passivation film are formed in succession, and

wherein the electroluminescence element is interposed between the first passivation film and the second passivation film.

66. (Canceled)

67. (Previously presented) A method according to claim 65 wherein each of the first passivation film and the second passivation film comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

68. (Currently Amended) A method according to claim 65 wherein each of the first passivation film and the second passivation film comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), ~~(La) lanthanum~~ La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium).

69. (Previously presented) A method according to claim 65 further comprising a step of forming an insulating film that comprises at least an element selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and an element selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus), between the substrate and the plurality of thin film transistors.

70. (Currently Amended) A method according to claim 65 further comprising a step of forming an insulating film that comprises Si, Al, N, O and M where M is a rare earth element preferably one selected from a group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), ~~(La) lanthanum~~ La (lanthanum), Gd (gadolinium), Dy (dysprosium) and Nd (neodymium), between the substrate and the plurality of thin film transistors.

71. (Currently Amended) A method for manufacturing a display device comprising the steps of:

forming a plurality of thin film transistors over a substrate;

forming a leveling film comprising a resin over the plurality of thin film transistors;

forming a passivation film over the leveling film; and

forming an electroluminescence element over the passivation film, said electroluminescence element comprising ~~an anode, a cathode~~ a first electrode formed in contact with the passivation film, a second electrode and a light emitting layer interposed therebetween[[.]],

wherein the light emitting layer is formed by an ink jet method.

72. (Canceled)

73. (Previously presented) A method according to claim 71 wherein said passivation film comprises a material selected from the group consisting of silicon nitride and silicon oxynitride.

74. (Previously presented) A method according to claim 71 wherein said electroluminescence material comprises an organic light emitting layer.

75. (Currently Amended) A method of manufacturing a display device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising silicon and nitrogen over the thin film transistor;

forming a leveling film comprising a resin over the first insulating film;

forming a second insulating film comprising silicon nitride;

forming a light emitting element over the second insulating film, said light emitting element comprising ~~an electroluminescence layer comprising an anode, a cathode~~ a first electrode formed in contact with the second insulating film, a second electrode and a light emitting layer comprising an organic material interposed therebetween; and

forming a third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide[[.]],

wherein the light emitting layer, the second electrode and the third insulating film are formed in succession.

76. (Currently Amended) A display device comprising:

a substrate;

a thin film transistor formed over the substrate, said thin film transistor comprising at least a semiconductor film and a gate electrode adjacent to the semiconductor film with a gate insulating film therebetween;

a first insulating film comprising silicon, nitrogen and oxygen formed over at least the semiconductor film and the gate electrode;

a leveling film comprising a resin formed over the first insulating film;

a second insulating film comprising silicon nitride formed on the leveling film;

a light emitting element formed on the second insulating film, said light emitting element comprising a first electrode formed [[on]] in contact with the second insulating film, an

electroluminescence layer comprising an organic material ~~adjacent to~~ over the first electrode and a second electrode formed over the electroluminescence layer; and

a third insulating film formed over the second electrode, said third insulating film comprising a material selected from the group consisting of aluminum nitride, silicon carbide, silicon nitride, boron nitride, boron phosphate and aluminum oxide.

77. (New) A display device according to claim 76, wherein a pixel electrode is formed between the first electrode and the second insulating film.

78. (New) A display device according to claim 76, wherein a storage capacitor is formed by the semiconductor film, the gate insulating film and a capacitor electrode.